



STGW38IH130D

33 A - 1300 V - very fast IGBT

Features

- Low saturation voltage
- High current capability
- Low switching loss
- Low static and peak forward voltage drop free-wheeling diode

Applications

- Induction cooking, microwave oven
- Soft switching application

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior. This device is well suited for the resonant or soft switching applications.

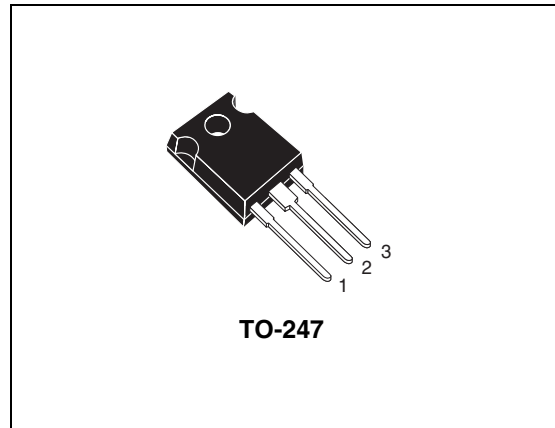


Figure 1. Internal schematic diagram

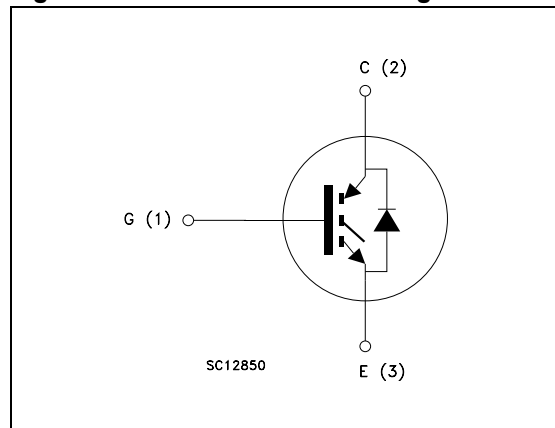


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGW38IH130D	GW38IH130D	TO-247 long leads	Tube
STGWS38IH130D		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Revision history	12

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-247 long leads	TO-247	
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	1300		V
$I_C^{(1)}$	Continuous collector current at $T_C = 25\text{ °C}$	63	55	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100\text{ °C}$	33	25	A
$I_{CL}^{(2)}$	Turn-off latching current	40		A
$I_{CP}^{(3)}$	Pulsed collector current	125		A
V_{GE}	Gate-emitter voltage	± 25		V
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	250	180	W
I_F	Diode RMS forward current at $T_C = 25\text{ °C}$	30		A
I_{FSM}	Surge non repetitive forward current $t_p = 10\text{ ms}$ sinusoidal	100		A
T_j	Operating junction temperature	-55 to 150		°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. $V_{clamp} = 960\text{ V}$, $T_j = 150\text{ °C}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$

3. Pulse width limited by maximum permissible junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-247 long leads	TO-247	
$R_{thj-case}$	Thermal resistance junction-case IGBT	0.5	0.7	°C/W
$R_{thj-case}$	Thermal resistance junction-case diode	2	2.1	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	50		°C/W

2 Electrical characteristics

($T_J = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	1300			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$ $V_{GE} = 15\text{ V}$, $I_C = 20\text{ A}$, $T_J = 125\text{ °C}$		2.1 2.0	2.8	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	3.75		5.75	V
I_{CES}	Collector-cut-off current ($V_{GE} = 0$)	$V_{CE} = 1300\text{ V}$ $V_{CE} = 1300\text{ V}$, $T_J = 125\text{ °C}$			1 10	mA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 25\text{ V}$, $I_C = 20\text{ A}$		20		S
V_F	Diode forward voltage	$I_F = 20\text{ A}$ $I_F = 20\text{ A}$, $T_J = 125\text{ °C}$		1.3	1.9 1.7	V V

1. Pulsed: pulse duration= 300 μs , duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	2900	-	pF
C_{oes}	Output capacitance			155		pF
C_{res}	Reverse transfer capacitance			30		pF
Q_g	Total gate charge	$V_{CE} = 960\text{ V}$, $I_C = 20\text{ A}$, $V_{GE} = 15\text{ V}$	-	127	-	nC
Q_{ge}	Gate-emitter charge			18		nC
Q_{gc}	Gate-collector charge			50		nC

Table 6. Inductive load switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$		102		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$,	-	284	-	ns
t_f	Current fall time	(see Figure 15)		180		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$		200		ns
$t_{d(off)}$	Turn-off delay time	$R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$,	-	424	-	ns
t_f	Current fall time	$T_J = 125\text{ }^\circ\text{C}$ (see Figure 15)		316		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{off}^{(1)}$	Turn-off switching losses	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, (see Figure 15)	-	3.4	-	mJ
$E_{off}^{(1)}$	Turn-off switching losses	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 15)	-	6.4	-	mJ

1. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

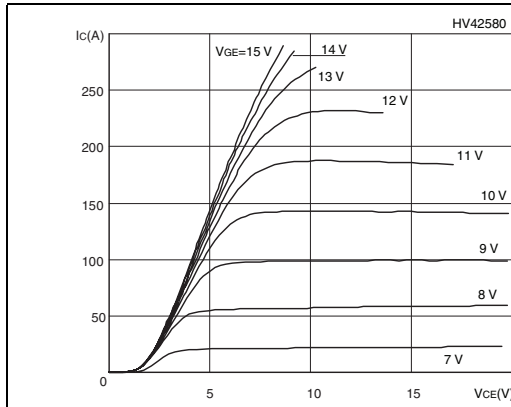


Figure 3. Transfer characteristics

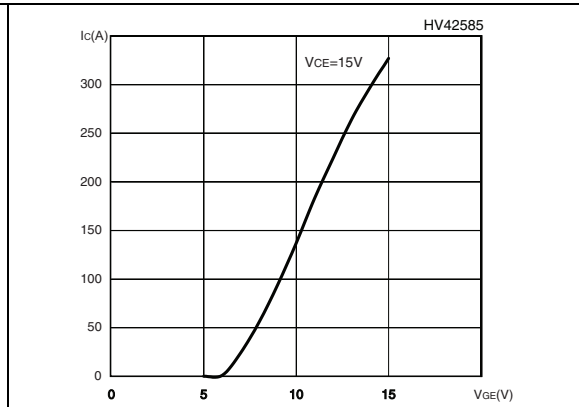


Figure 4. Transconductance

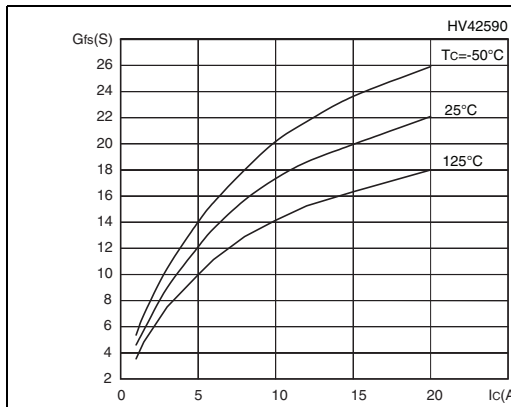


Figure 5. Collector-emitter on voltage vs temperature

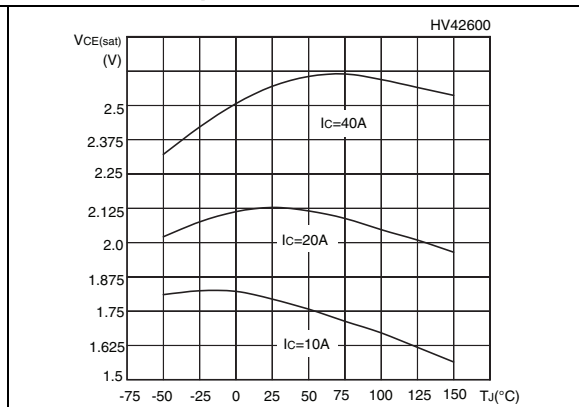


Figure 6. Normalized breakdown voltage vs temperature

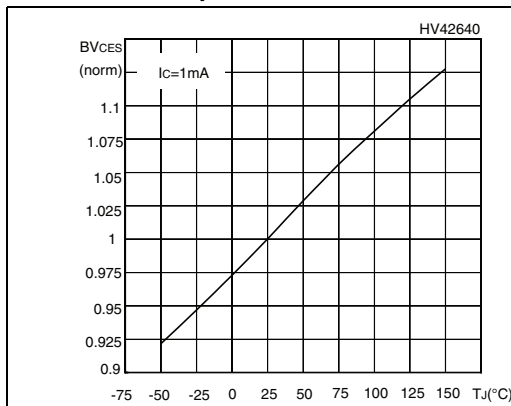


Figure 7. Gate-charge vs gate-emitter

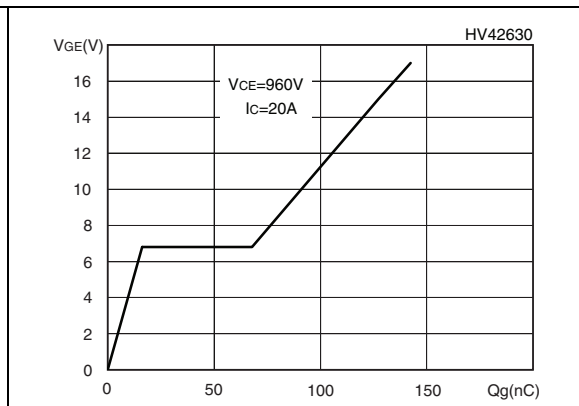


Figure 8. Normalized gate threshold voltage vs temperature

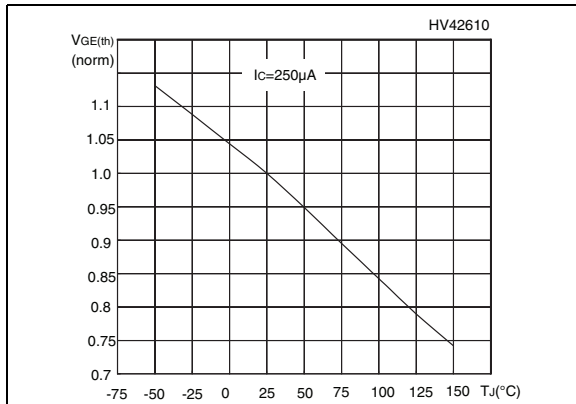


Figure 9. Collector-emitter on voltage vs collector current

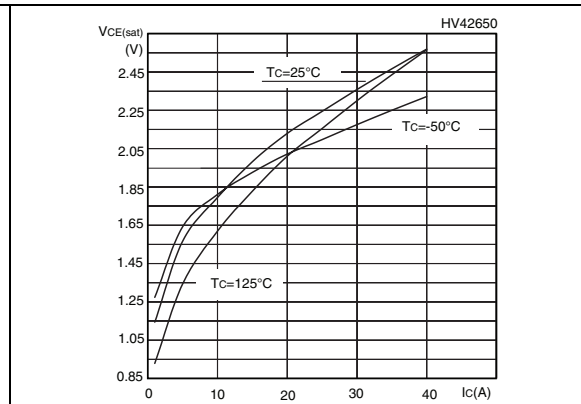


Figure 10. Switching losses vs temperature

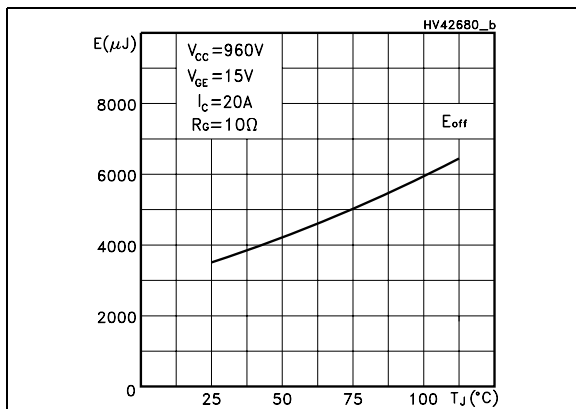


Figure 11. Switching losses vs gate resistance

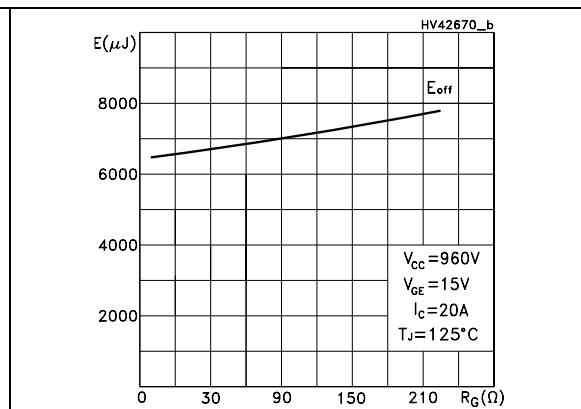


Figure 12. Switching losses vs collector current

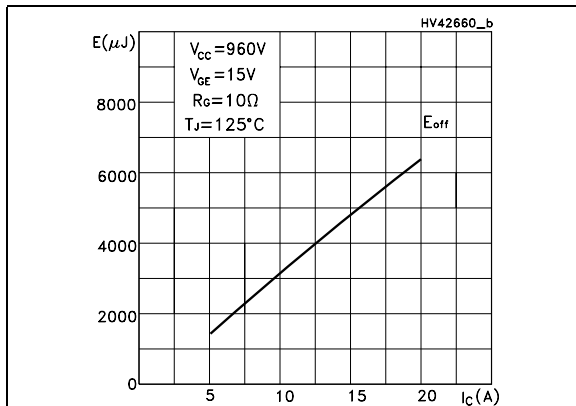


Figure 13. RBSOA

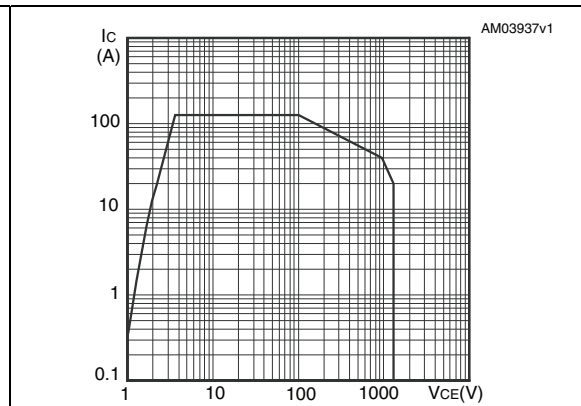
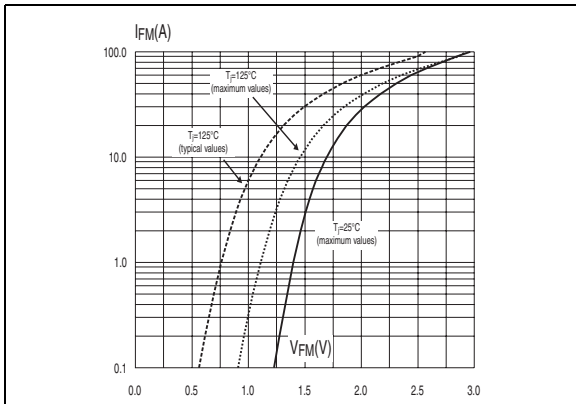


Figure 14. Emitter-collector diode characteristics



3 Test circuits

Figure 15. Test circuit for inductive load switching

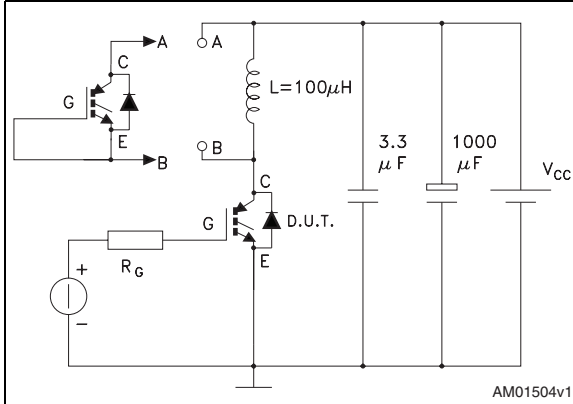


Figure 16. Gate charge test circuit

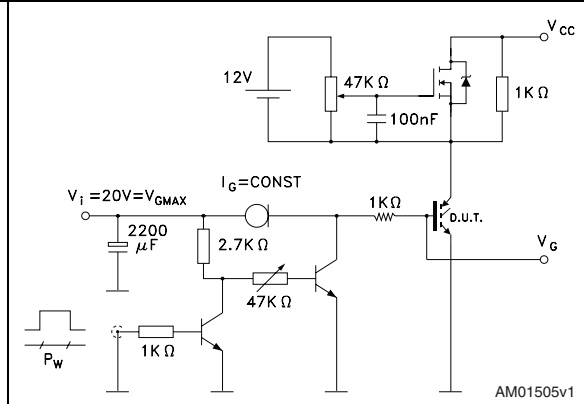
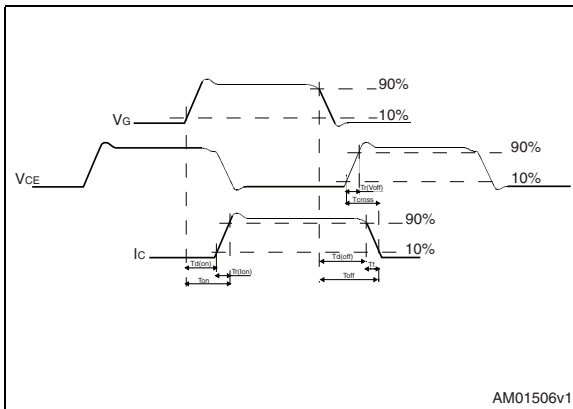


Figure 17. Switching waveform

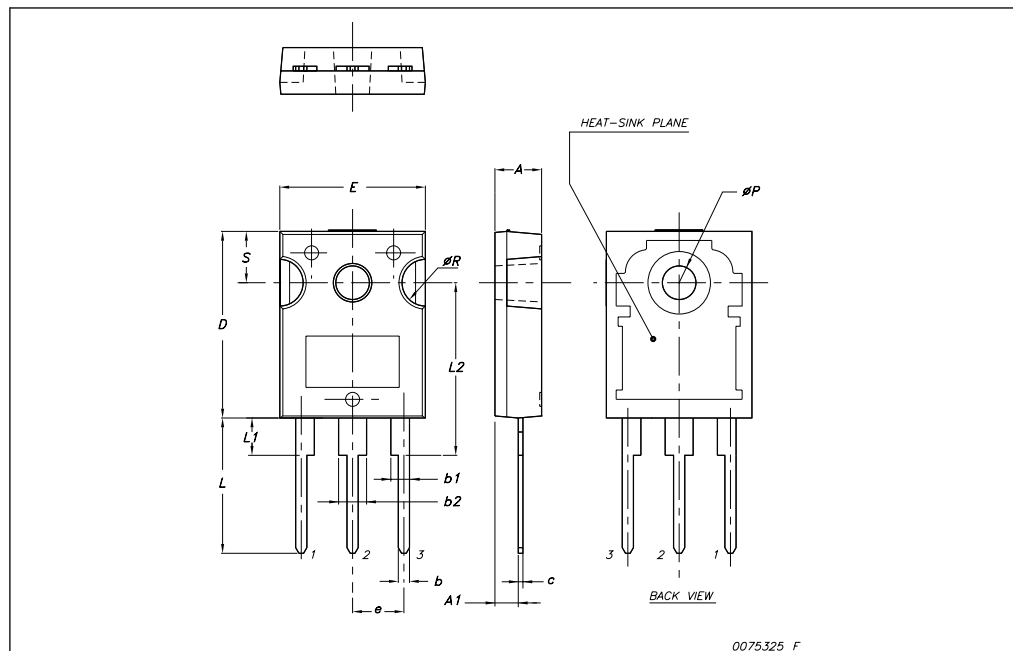


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

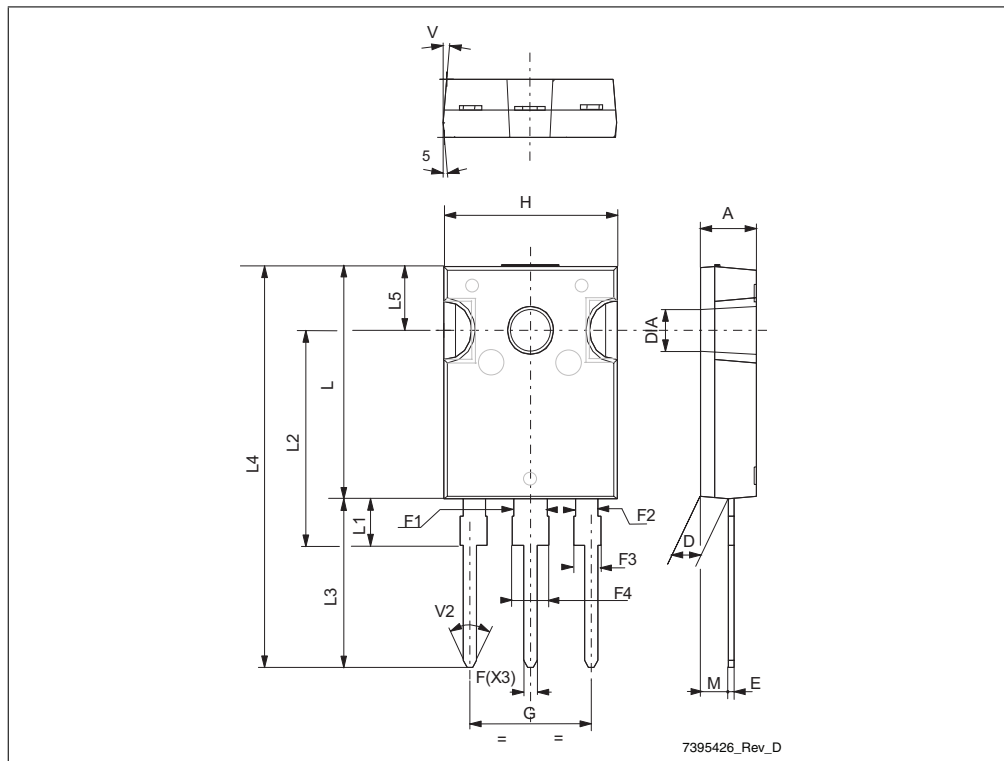
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.16
D	2.2		2.6
E	0.4		0.8
F	1		1.4
F1		3	
F2		2	
F3	1.9		2.4
F4	3		3.4
G		10.9	
H	15.45		16.03
L	19.85		21.09
L1	3.7		4.3
L2	18.3		19.13
L3	14.2		20.3
L4	34.05		41.38
L5	5.35		6.3
M	2		3
V		5°	
V2		60°	
DIAM	3.55		3.65



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-May-2009	1	Initial release
16-Jul-2009	2	Document status promoted from preliminary data to datasheet.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com